

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Bruno GHYSELEN *et al.*

Application No.:

Group Art Unit:

Filing Date: Concurrently herewith

Examiner:

For: PROCESS FOR TRANSFERRING A  
LAYER OF STRAINED  
SEMICONDUCTOR MATERIAL

Attorney Docket No.: 4717-7500

**INFORMATION DISCLOSURE STATEMENT**

**MS PATENT APPLICATION**

Commissioner for Patents  
Washington, D.C. 20231


Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed are copies of sixteen (16) references listed on the enclosed Form PTO-1449 for the Examiner's review. Also enclosed is a copy of the preliminary International Search Report from the French priority application on which some of the references were cited. It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the these references. Should any fees be required, however, please charge such fees to Winston & Strawn Deposit Account No. 501-814.

Respectfully submitted,

July 9, 2003  
Date

  
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E. Bradley Gould (Reg. No. 41,792)  
For: Allan A. Fanucci (Reg. No. 30,256)

**WINSTON & STRAWN**  
**Customer No. 28765**

202-371-5771

<b>LIST OF REFERENCES CITED BY APPLICANT</b> <b>Form PTO-1449</b> (Use several sheets if necessary)				ATTY. DOCKET NO.:		APPLICATION NO.:		
				<b>4717-7500</b>				
Sheet 1 of 1				APPLICANT:				
				<b>Bruno GHYSELEN et al.</b>				
				FILING DATE:		GROUP:		
				<b>Concurrently herewith</b>				
<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	A	6,573,126	06/2003	Cheng et al.	438	149		
	B	6,524,935	02/2003	Canaperi et al.	438	478		
	C	6,410,371	06/2002	Yu et al.	438	151		
	D	6,403,450	06/2002	Maleville et al.	438	471		
	E	6,323,108	11/2001	Kub et al.	438	458		
	F	6,059,895	05/2000	Chu et al.	148	33.1		
	G	5,882,987	03/1999	Srikrishnan	438	458		
	H	5,013,681	05/1991	Godbey et al.	437	86		
<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	I	2 365 214	02/2002	Great Britain				
	J	01/99169	12/2001	WO				
	K	01/11930	02/2001	WO				
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
	L	L.J. Huang et al., <i>SiGe-On-Insulator Prepared by Wafer Bonding and Layer Transfer for High Performance Field-Effect Transistors</i> , Applied Physics Letters, February 26, 2002, Vol 78, No. 9						
	M	Zhi-Yuan Cheng et al. of Massachusetts Institute of Technology has presented, in a document entitled <i>SiGe-On-Insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation</i> (2001 IEEE International SOI Conference, 10/01)						
	N	T. A. Langdo et al., <i>SiGe-Free Strained Si On Insulator by Wafer Bonding and Layer Transfer</i>						
	O	Patent Application Publication No. US 2002/0140031 A1, published October 3, 2002						
	P	Patent Application Publication No. US 2002/0030227 A1, published March 14, 200 2						
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								